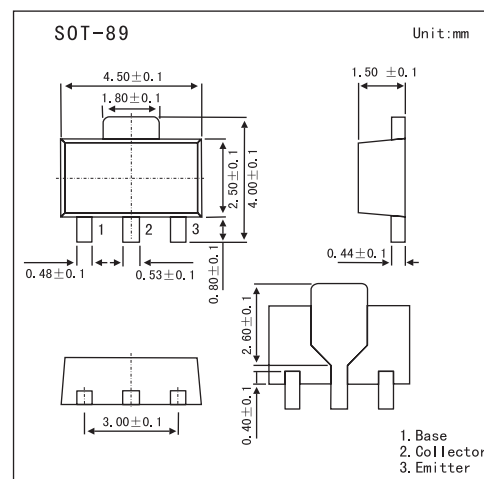


Silicon PNP Epitaxial Planar Type

2SB767

■ Features

- Large collector power dissipation P_C
- High collector-emitter voltage (Base open) V_{CEO}
- Mini type package, allowing downsizing of the equipment and automatic



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-80	V
Collector-emitter voltage	V_{CEO}	-80	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-1	A
Peak collector current	I_{CP}	-0.5	A
Collector power dissipation	P_C	1	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base cutoff current	I_{CBO}	$V_{CB} = -20\text{ V}, I_E = 0$			-0.1	μA
Collector-base voltage	V_{CBO}	$I_C = -10\mu\text{A}, I_E = 0$	-80			V
Collector-emitter voltage	V_{CEO}	$I_C = -100\mu\text{A}, I_B = 0$	-80			V
Emitter-base voltage	V_{EBO}	$I_E = -10\mu\text{A}, I_C = 0$	-5			V
Forward current transfer ratio	h_{FE}	$V_{CE} = -10\text{ V}, I_C = -150\text{ mA}$	90		220	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -300\text{ mA}, I_B = -30\text{ mA}$		-0.2	-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -300\text{ mA}, I_B = -30\text{ mA}$		0.85	-1.2	V
Transition frequency	f_T	$V_{CB} = -10\text{ V}, I_E = 50\text{ mA}, f = 200\text{ MHz}$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$		20	30	pF

■ h_{FE} Classification

Marking	CQ	CR
h_{FE}	90~155	130~220